

NPN Transistors

6501130 NATL SEMICOND, (DISCRETE)

28C 35387 D

T-35-01

SATURATED SWITCHES



Type No.	Case Style	V _{CE0} (V)		V _{BE0} (V)	I _{CS} * (mA)		h _{FE}		V _{CE(SAT)} & V _{BE(SAT)} (V)		I _C (mA)	C _{ob} (pF)		f _T (MHz)		t _{off} (ns)	Test Conditions	Process No.	
		Min	Max		Min	Max	Min	Max	Min	Max		Min	Max	Min	Max				
2N706	TO-18	25	15	5	500	15	20	10	1	0.6	0.7	0.9	10	6	200	10	75	2	21
2N743	TO-52		12		1 μA	20	10	100	1	0.65	0.85	10	5	300	10	24	1	21	
2N744	TO-52	20	12	5	1 μA	20	20	100	1	0.65	0.85	10	5	280	10	24	1	21	
2N753	TO-52	25	15	5	500	15	40	120	1	0.6	0.7	0.9	10	5	200	10	75	2	21
2N834	TO-52	40	15	5	500	20	25	10	1	0.25	0.9	10	4	350	10	30	2	21	
2N2369	TO-52	40	15	4.5	400	20	20	100	2	0.25	0.7	0.85	10	4	500	10	18	1	21
2N2369A	TO-18	40	15	4.5	400*	20	20	120	1	0.2	0.7	0.85	10	4	500	10	18	1	21
2N3011	TO-52	30	12	5	400*	20	12	100	1	0.2	0.72	0.85	10	4	400	20	20	4	21
2N3605	TO-92 (94)		14		500	18	30	120	0.4	0.25	1.5	30	6	300	10	45	2	21	
2N3606	TO-92 (94)		14		500	18	30	120	1	0.25	0.6	0.9	10	6	300	10	60	2	21
2N3607	TO-92 (94)		14		500	18	30	10	1	0.25	0.85	10	6	300	10	70	2	21	
2N4274	TO-92 (92)				Same as PN4274, see page 1-3 for explanation														
2N4275	TO-92 (92)				Same as PN4275, see page 1-3 for explanation														
2N4294	TO-92 (94)	30	12	4.5	400	20	20	100	2	0.25	0.6	0.9	10	5	400	10	20	1	21
2N4295	TO-92 (94)	40	15	5	100	20	20	100	2	0.25	0.6	0.9	10	4	500	10	15	1	21
2N5030	TO-92 (94)	30	12	4	250	20	30	10	1	0.25	0.72	0.87	10	4	400	10	30	9	21
2N5134	TO-92 (92)				Same as PN5134, see page 1-3 for explanation														
2N5224	TO-92 (92)	25	12	5	500	15	15	100	1	0.35	0.9	10	4	250	10	60	11	21	

6501130 NATL SEMICOND, (DISCRETE)

SATURATED SWITCHES (Continued)

Type No.	Case Style	V _{CE} * V _{CE0} (V) Min	V _{BE0} (V) Min	I _{CE} * I _{CE0} (mA) Max	V _{CE} (V) & V _{BE} (V)	h _{FE} @ I _C (mA) & V _{CE} (V)	I _C (mA) @ I _B = I _C /10	C _{ob} (pF) Max	f _T (MHz) Min	I _C (mA) @ I _B = I _C /10	t _(off) (ns) Max	Test Conditions	Process No.
2N5769	TO-92 (92)	40	4.5	400	20	100	10	4	500	10	18	1	21
2N5772	TO-92 (92)	40	5	500	20	300	30	5	350	30	28	3	21
MPS706	TO-92 (92)	15	3	500	15	10	10	6	200	10	75	11	21
MPS834	TO-92 (92)	40	5	500	20	10	10	4	350	10	30	2	21
MPS2369	TO-92 (92)	40*	4.5	400	20	100	10	4	500	10	18	7	21
MPS2713	TO-92 (92)	18	5	500	18	2	4.5						21
MPS2714	TO-92 (92)	18	5	500	18	2	4.5						21
MPS3646	TO-92 (92)	Same as PN3646, see page 1-4 for explanation											
PN2369	TO-92 (92)	40*	4.5	400	20	100	10	4	500	10	18	1	21
PN2369A	TO-92 (92)	40*	4.5	30	20	100	10	4	500	10	18	1	21
PN4274	TO-92 (92)	30*	4.5	500	20	100	10	4	400	10	12	12	21
PN4275	TO-92 (92)	40*	4.5	500	20	100	10	4	400	10	12	12	21
PN5134	TO-92 (92)	20*	3.5	100	15	30	0.4	4	250	10	18	12	21
2N708	TO-52	40	5	25	20	10	0.5	6	300	10			22

TEST CONDITIONS:

(1) V_{CC} = 3V, I_C = 10 mA, I_B = 3 mA, I_B = 1.5 mA. (2) V_{CC} = 3V, I_C = 10 mA, I_B = 3 mA, I_B = 1 mA. (3) V_{CC} = 10V, I_C = 300 mA, I_B = 30 mA. (4) V_{CC} = 2V, I_C = 30 mA, I_B = 3 mA. (5) V_{CC} = 25V, I_C = 30 mA, I_B = 3 mA. (6) V_{CC} = 25V, I_C = 500 mA, I_B = 50 mA. (7) V_{CC} = 30V, I_C = 500 mA, I_B = 50 mA. (8) V_{CC} = 30V, I_C = 1A, I_B = 100 mA. (9) V_{CC} = 3V, I_C = 10 mA, I_B = 1 mA, I_B = 1 mA. (10) V_{CC} = 10.7V, I_C = 1A, I_B = 100 mA. (11) V_{CC} = 3V, I_C = 10 mA, I_B = 3 mA. (12) V_{CC} = 3V, I_C = 10 mA, I_B = 3.3 mA.

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SATURATED SWITCHES (Continued)

Type No.	Case Style	V _{CE(S)} V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CE(S)} I _{CB0} (mA) Max	I _{CE} & V _{CE} (mA) & (V)	V _{CE(SAT)} & V _{BE(SAT)} (V) & (V) Max	I _C (mA) (I _B = I _C /10)	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Max	t _(off) (ns) Max	Test Conditions	Process No.
2N3009	TO-52	40	15	4	500*	1 300 0.5 100 0.4 30	0.18 0.95 0.28 1.2 0.5 1.7	30 100 300 300	5	350	30	25	3	22
2N3013	TO-52	40	15	5	300*	1 300 0.5 100 0.4 30	0.18 0.95 0.28 1.2 0.5 1.7	30 100 300 300	5	350	30	25	3	22
2N3646	Same as PN3646, see below for explanation													
PN3646	TO-92 (92)	40*	15	5	500*	1 300 0.5 100 0.4 30	0.2 0.95 0.28 1.2 0.5 1.7	30 100 300 300	5	350	30	28	3	22
2N3015	TO-39	60	30	5	200	0.7 300 1.0 150	0.4 1.2 1.0 1.6	150 500	8	250	50	60	5 & 6	25
2N3252	TO-39	60	30	5	500	5 750 1 500 1 150	0.3 1.0 0.5 0.7 1.0 1.8	150 500 1A 1A	12	200	50	70	7	25
2N3253	TO-39	75	40	5	500	5 750 1 375 1 150	0.35 1.0 0.6 0.7 1.2 1.8	150 500 1A 1A	12	175	50	70	7	25
2N3444	TO-39	80	50	5	500	5 750 1 375 1 150	0.35 1.0 0.6 0.7 1.2 1.8	150 500 1A 1A	12	150	50	70	7	25
2N3724	TO-39	50	30	6	1.7 μA	5 1A 2 800 1 500 1 300 1 100 1 100	0.32 1.1 0.42 0.9 0.65 1.5 0.75 1.7	300 500 800 800 800 800 1A 1A	300	300	50	60	7	25
2N3724A	TO-39	50	30	6	500	5 1.5A 5 1A 2 800 1 500 1 300 1 100 1 100	0.32 1.1 0.42 0.9 0.65 1.5 0.75 1.7	300 500 800 800 800 800 1A 1A	12	300	50	50	8	25
2N3725	TO-39	80	50	6	1.7 μA	5 1A 2 800 1 500 1 300 1 100 1 100	0.4 1.1 0.52 0.9 0.8 1.5 0.95 1.7	300 500 800 800 800 800 1A 1A	10	300	50	60	7	25

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28C 35390

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SATURATED SWITCHES (Continued)

Type No.	Case Style	V _{CE} * V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	IC _{BO} * (mA) Max	IC _{BO} @ (V)	h _{FE} Min	IC @ (mA) Max	V _{CE} (V) Max	V _{BE(SAT)} & (V) Min	V _{BE(SAT)} @ (V) Max	IC (mA) (I _B = I _C /10) Max	C _{ob} (pF) Max	f _T (MHz) Min	IC (mA) Max	t _(off) (ns) Max	Test Conditions	Process No.
2N3725A	TO-39	80	50	6	500	60	20	1.5A	0.4	1.1	1.1	300	10		50	50	8	25
DH3724CD	Ceramic DIP (40)	50*	36	60	1.7 μA	40	30	1A	0.75	1.7	1.7	500	12	300	50	60	7	25
DH3724CN	Molded DIP (39)	Electrical same as DH3724CD																
DH3725CD	Ceramic DIP (40)	80*	50	6	1.7 μA	60	25	1A	0.95	1.7	1.7	500	10	250	50	60	7	25
DH3725CN	Molded DIP (39)	Electrical same as DH3725CD																
2N4013	TO-18	50	30	6	1.7 μA	40	30	1A	0.25	0.76	0.76	10	12	300	50	60	7	25
2N4014	TO-18	80	50	6	1.7 μA	60	25	1A	0.25	0.76	0.76	10	10	300	50	60	7	25
							20	800	0.26	0.86	100							
2N4047	TO-39	80	50	6	1.7 μA	60	35	500	0.4	1.1	1.1	300						25
							40	300	0.25	0.9	1.2	500						
2N4047	TO-39	80	50	6	1.7 μA	60	60	100	0.8	1.5	1.5	800						25
							30	10	0.9	1.7	1A							
2N4047	TO-39	80	50	6	1.7 μA	60	15	1A	0.4	1.1	1.1	300	10	250	50	60	7	25
							15	800	0.52	0.9	1.2	500						
2N4047	TO-39	80	50	6	1.7 μA	60	30	300	0.8	1.5	1.5	800						25
							40	100	0.95	1.7	1A							

TEST CONDITIONS:

(1) V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1.5 mA. (2) V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1 mA. (3) V_{CC} = 10V, I_C = 300 mA, I_B¹ = I_B² = 30 mA. (4) V_{CC} = 2V, I_C = 30 mA, I_B¹ = I_B² = 3 mA.
 (5) V_{CC} = 25V, I_C = 300 mA, I_B¹ = I_B² = 30 mA. (6) V_{CC} = 25V, I_C = 500 mA, I_B¹ = I_B² = 50 mA. (7) V_{CC} = 30V, I_C = 500 mA, I_B¹ = I_B² = 50 mA. (8) V_{CC} = 30V, I_C = 1A, I_B¹ = I_B² = 100 mA.
 (9) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 1 mA. (10) V_{CC} = 10.7V, I_C = 1A, I_B¹ = I_B² = 100 mA. (11) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3 mA. (12) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3.3 mA.

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28C 35391 D

SATURATED SWITCHES (Continued)

Type No.	Case Style	V _{CE(S)}		V _{CEO} (V) Min	V _{BE(S)}		h _{FE} @ I _C & V _{CE} (V)	I _{CS} * I _{CBO} (nA) Max	V _{BO} (V) Min	I _C (mA) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) @ I _C (mA)		C _{ob} (pF) Max	f _T (MHz) @ I _C (mA)		t _{off} (ns) Max	Test Conditions	Process No.
		Min	Max		Min	Max						Min	Max		Min	Max			
2N5189	TO-39	60	35	5	30	30	15	500	30	1A	1.0	1.5	1A	12	250	50	70	10	25
2N6737	TO-237 (EBC)	80	45	6	60	60	35	1.7 μA	1	500	0.52	0.8	1.1	10	300	50	60	7	25

TEST CONDITIONS:

(1) V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1.5 mA. (2) V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1 mA. (3) V_{CC} = 10V, I_C = 300 mA, I_B¹ = I_B² = 30 mA. (4) V_{CC} = 2V, I_C = 30 mA, I_B¹ = I_B² = 3 mA. (5) V_{CC} = 25V, I_C = 300 mA, I_B¹ = I_B² = 30 mA. (6) V_{CC} = 25V, I_C = 500 mA, I_B¹ = I_B² = 50 mA. (7) V_{CC} = 30V, I_C = 500 mA, I_B¹ = I_B² = 50 mA. (8) V_{CC} = 30V, I_C = 1A, I_B¹ = I_B² = 100 mA. (9) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 1 mA. (10) V_{CC} = 10.7V, I_C = 1A, I_B¹ = I_B² = 100 mA. (11) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3 mA. (12) V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3.3 mA.

RF AMPS AND OSCILLATORS

Type No.	Case Style	V _{CE(S)}		V _{CEO} (V) Min	V _{BE(S)}		h _{FE} @ I _C & V _{CE} (V)	I _{CS} * I _{CBO} (nA) Max	V _{BO} (V) Min	I _C (mA) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) @ I _C (mA)		C _{ob} /C _{re} (pF) Min Max	f _T (MHz) @ I _C (mA)		NF (dB) @ (MHz) Max	Process No.		
		Min	Max		Min	Max						Min	Max		Min	Max				
2N2857	TO-72	30	15	2.5	15	15	30	10	15	3	1	1.0	10	1	1000	1900	5	4.5	42	
2N3478	TO-72	30	15	2	15	15	25	150	2	8	1	1.0	10	1	750	1600	5	4.5	42	
2N3600	TO-72	30	15	3	10	15	20	150	3	1	1	1.0	10	1	850	1500	5	4.5	42	
2N3932	TO-72	30	20	2.5	10	15	40	150	2	8	0.55	0.75	1600	2	4.5	750	1600	2	4.5	42
2N3933	TO-72	40	30	2.5	10	15	60	200	2	8	0.55	0.75	1600	2	4	750	1600	2	4.5	42
2N4259	TO-72	40	30	2.5	10	15	60	250	2	8	0.55	0.75	1600	2	4	750	1600	2	4.5	42
2N5179	TO-72	20	12	2.5	20	15	25	250	3	1	0.4	1.0	10	1	900	2000	5	4.5	42	
2N5180	TO-72	30	15	2	500	8	20	200	2	8	1	1.0	10	1	650	1700	2	4.5	42	
40235	TO-72	35	3	3	1 μA	35	40	170	1	6	0.65								42	
40236	TO-72	35	3	3	1 μA	35	40	275	1	6	0.65								42	
40237	TO-72	35	3	3	1 μA	35	27	275	1	6	0.8								42	
40238	TO-72	35	3	3	1 μA	35	40	170	1	6	0.65								42	
40239	TO-72	35	3	3	1 μA	35	27	100	1	6	0.65								42	

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28C 35392
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RF AMPS AND OSCILLATORS (Continued)



Type No.	Case Style	V _{CE0} [*] (V) Min	V _{CE0} [*] (V) Min	V _{EBO} (V) Min	I _{CB0} (mA) Max	V _{CB} (V) Max	h _{FE} Min	I _C (mA) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Max	I _C (mA) Max	C _{ob/Cre} (pF) Min	f _T (MHz) Min	I _C (mA) Max	NF (dB) Max	Freq (MHz) @	Process No.		
40240	TO-72	35	3	3	1 μA	35	27	275	1	6		0.65					42		
40242	TO-72	35	3	3	20	1	40	170	1	6		0.65					42		
MPS6539	TO-92 (91)	20	20		50	15	20	4	10			0.7	500	4	4.5	100	42		
MPS6548	TO-92 (91)	30	25	3	100	25	25	4	10	0.5	0.95	0.7	650	4			42		
MPSH10	TO-92 (91)	30	25	3	100	25	60	4	10	0.5		0.35	650	4			42		
MRF501	TO-72	25	15	3.5	50	1	30	250	1	6			600	5			42		
MRF502	TO-72	35	15	3.5	20	1	40	170	1	6			800	5			42		
PN5179	TO-92 (91)	20	15	2.5	2	15	25	250	3	1	0.4	1.0	900	2000	4.5	200	42		
2N917	TO-72	30	15	3	1	15	20	3	1	0.5	0.87	3	500	4	6	60	43		
2N918	TO-72	30	15	3	10	15	20	3	1	0.4	1.0	3	600	4	6	60	43		
2N3563	TO-92 (92)	Same as PN3563, see page 1-8 for explanation																	
2N3564	TO-92 (92)	Same as PN3564, see page 1-8 for explanation																	
2N3662	TO-92 (94)	18	12	3	500	15	20	8	10			0.8	1.7	700	2100	5	6.5	60	43
2N3663	TO-92 (94)	30	12	3	500	15	20	8	10			0.8	1.7	700	2100	5	6.5	60	43
2N3825	TO-92 (94)	30	15	4	100	15	20	2	10	0.25	2	3.5	200	800	2	5.5	1	43	
2N4292	TO-92 (94)	30	15	3	500	15	20	3	1	0.6	10	3.5	600	4	6	60	43		
2N4293	TO-92 (94)	30	15	3	500	15	20	3	1	0.6	10	3.5	600	4	6	60	43		
2N5130	TO-92 (92)	Same as PN5130, see page 1-8 for explanation																	
2N5770	TO-92 (92)	30	15	4.5	10	15	50	200	8	10	1.0	0.7	1.1	900	1800	8	6	60	43
MPS3563	TO-92 (92)	Same as PN3563, see page 1-8 for explanation																	
MPS6507	TO-92 (92)	30*	20		5	15	25	2	10			2.5	700	10			43		

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RF AMPS AND OSCILLATORS (Continued)

Type No.	Case Style	V _{CE} * V _{CB0} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CB0} (mA) Max	h _{FE} Min	I _C & V _{CE} (mA) & (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	I _C (mA) Max	C _{ob/Cre} (pF) Min	f _T (MHz) Min	I _C (mA) Max	NF (dB) Max	Freq (MHz)	Process No.
MPS6511	TO-92 (92)	30*	20		50	25	10 10				2.5					43
MPS6541	TO-92 (92)	30*	20	4	50	25	4 10				1.7	600	1500	4		43
PN918	TO-92 (92)	30	15	3	10	20	3 1	0.4	1.0	10	1.7	600	4	6	60	43
PN3563	TO-92 (92)	30	15	2	50	20	8 10				1.7	600	1500	8		43
PN3564	TO-92 (92)	30	15	4	50	20	15 10	0.3	0.97	20	3.5	400	1200	15		43
PN5130	TO-92 (92)	30	12	1	50	15	8 10	0.6	1.0	10	1.7	450	8			43
2N4134	TO-72	30	30	3	50	25	4 5				0.5	350	800	4	2.5	60
2N4135	TO-72	30	30	3	50	25	4 5				0.5	425	800	4	5	450
MPS6568A	TO-92 (91)	20	20	3	50	20	4 5	0.3	0.96	10	0.65	375	800	4	3.3	200
MPS6569	TO-92 (91)	20	20	3	50	20	4 5	3	0.96	10	0.25	300	800	4	6	45
MPS6570	TO-92 (91)	20	20	3	50	20	4 5	3	0.96	10	0.25	300	800	4	6	45
MPSH30	TO-92 (91)	20	20	3	50	20	4 5	0.3	0.96	10	0.65	300	800	4	6	45
MPSH31	TO-92 (91)	20	20	3	50	20	4 5	0.3	0.96	10	0.65	300	800	4	6	45
SE5020	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	375	800	4	3.3	200
SE5021	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	375	800	4	4	200
SE5022	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4		
SE5023	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4	6	45
SE5024	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4	6	45
SE5050	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4	4	100
SE5051	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4		
SE5052	TO-72	20	20	3	50	20	4 5	3.0	0.96	10	0.25	300	800	4	4	200
MPSH32	TO-92 (96)	30	30	4	50	27	4 5	0.3	1.2	10	0.22	300	4			45
SE5055	TO-72	20	20	3	50	20	2 10	2.75		10	0.22	300	2	5	45	45
PE5025	TO-92 (92)	30	30	3	50	20	100 10	0.6		20	0.6	300	700	10		46

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RF AMPS AND OSCILLATORS (Continued)

Type No.	Case Style	V _{CE} * V _{CBO} (V) Min	V _{CEO} (V) Min	V _{EB0} (V) Min	I _{CBO} (mA) Max	V _{CB} (V)	h _{FE} Min	I _C (mA) Max	V _{CE} (V) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Max	I _C (mA) Max	C _{ob/Cre} (pF) Min	f _T (MHz) Min	I _C (mA) Max	NF (dB) Max	Freq (MHz) Max	Process No.
MPS6542	TO-92 (96)	30*	20		50	15	25	2	10			10	1.5	700				47
MPS6543	TO-92 (96)	35	20	3	100	25	25	4	10	0.35	0.95	4	1	750				47
MPS6546	TO-92 (96)	35	25	3	100	25	20	2	10	0.35		2	0.45	600				47
MPS6547	TO-92 (96)	35	25	3	100	25	20	2	10	0.35		2	0.35	600				47
MPSH11	TO-92 (96)	30	25	3	100	25	60	4	10	0.5		4	0.6	650	4			47
MPSH19	TO-92 (96)	30	25	3	100	15	45	4	10			4	0.65	300				47
MPSH24	TO-92 (96)	40	30	4	50	15	30	8	10			8	0.36	400				47
MPSH34	TO-92 (96)	45	45	4	50	30	15	20	2	0.5		15	0.32	500				47
PE3100	TO-92 (96)	30*	30	3	200	30	30	225	5	10		5	0.8	500				47
PE5029	TO-92 (96)	30	30	3	200	30	30	225	5	10		5	0.4	500		6	45	47
PE5030B	TO-92 (96)	45	40	4.5	100	30	45	150	7	15		7	0.25	600				47
PE5031	TO-92 (96)	40	30	4	100	30	30	180	5	10	1	10	0.4	500		4.5	200	47
TIS86	TO-92 (98)	30	30		100	15	40	200	4	10	0.5	15	0.45	500		5	200	47
TIS87	TO-92 (98)	45	45		100	15	30	150	12	12	0.5	15	0.45	500				47
MPS6540	TO-92 (91)	30	30	4	100	25	25	2	10	0.5		2	0.65	350				49
MPS6544	TO-92 (91)	60	45	4	500	35	20	30	10	0.5		30	0.65					49
MPS6567	TO-92 (91)		40	5	500	35	25	10	5	0.5		10	0.7					49
MPSH20	TO-92 (91)	40	30	4	50	15	25	4	10	0.95		4	0.65	400				49
*MPSH37	TO-92 (91)		40	5	500	35	25	5	10	0.5		10	0.7	300				49

NPN Transistors

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